

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

EFC4618R — General-Purpose Switching Device Applications

Features

- 2.5V drive
- · Best suited for LiB charging and discharging switch
- · Common-drain type

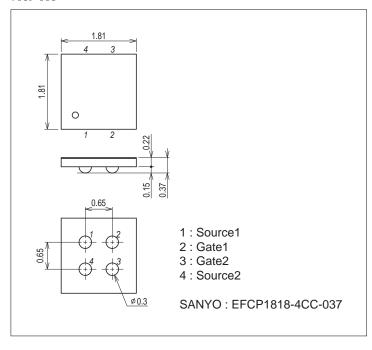
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	VSSS		24	V
Gate-to-Source Voltage	VGSS		±12	V
Source Current (DC)	IS		6	А
Source Current (Pulse)	ISP	PW≤10μs, duty cycle≤1%	60	Α
Total Dissipation	PT	When mounted on ceramic substrate (5000mm ² x0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7069-001



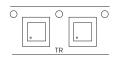
Product & Package Information

• Package : EFCP

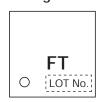
• JEITA, JEDEC :-

• Minimum Packing Quantity : 5,000 pcs./reel

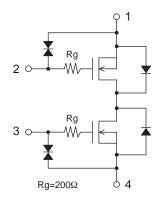
Packing Type: TR



Marking



Electrical Connection

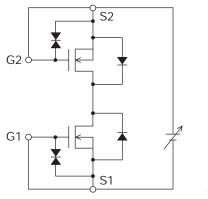


Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions		Ratings			11-4
Parameter	Symbol			min	typ	max	Unit
Source-to-Source Breakdown Voltage	V(BR)SSS	IS=1mA, VGS=0V	Test Circuit 1	24			V
Zero-Gate Voltage Source Current	ISSS	V _{SS} =20V, V _{GS} =0V	Test Circuit 1			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VSS=0V	Test Circuit 2			±10	μΑ
Cutoff Voltage	VGS(off)	V _{SS} =10V, I _S =1mA	Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	yfs	VSS=10V, IS=3A	Test Circuit 4		6.5		S
Static Source-to-Source On-State Resistance	R _{SS} (on)1	IS=3A, VGS=4.5V	Test Circuit 5	13.5	19.8	23	mΩ
	RSS(on)2	IS=3A, VGS=4.0V	Test Circuit 5	14	20.5	24	$m\Omega$
	RSS(on)3	I _S =3A, V _{GS} =3.7V	Test Circuit 5	14.5	21	25.5	mΩ
	RSS(on)4	IS=3A, VGS=3.1V	Test Circuit 5	14.9	23	30	mΩ
	RSS(on)5	I _S =3A, V _{GS} =2.5V	Test Circuit 5	18.5	27	35	$m\Omega$
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.	Test Circuit 7		200		ns
Rise Time	t _r	See specified Test Circuit.	Test Circuit 7		815		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.	Test Circuit 7		1840		ns
Fall Time	tf	See specified Test Circuit.	Test Circuit 7		1770		ns
Total Gate Charge	Qg	V _S S=10V, V _G S=4.5V, I _S =6A			25.4		nC
Forward Source-to-Source Voltage	V _F (S-S)	I _S =3A, V _{GS} =0V	Test Circuit 6		0.76	1.2	V

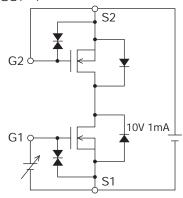
Test circuits are example of measuring FET1 side





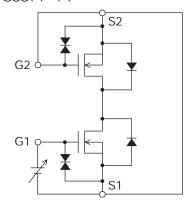
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Test Circuit 3 VGS(off)



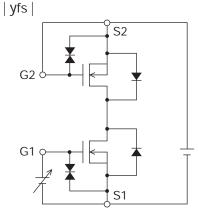
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Test Circuit 2 IGSS(+) / (--)

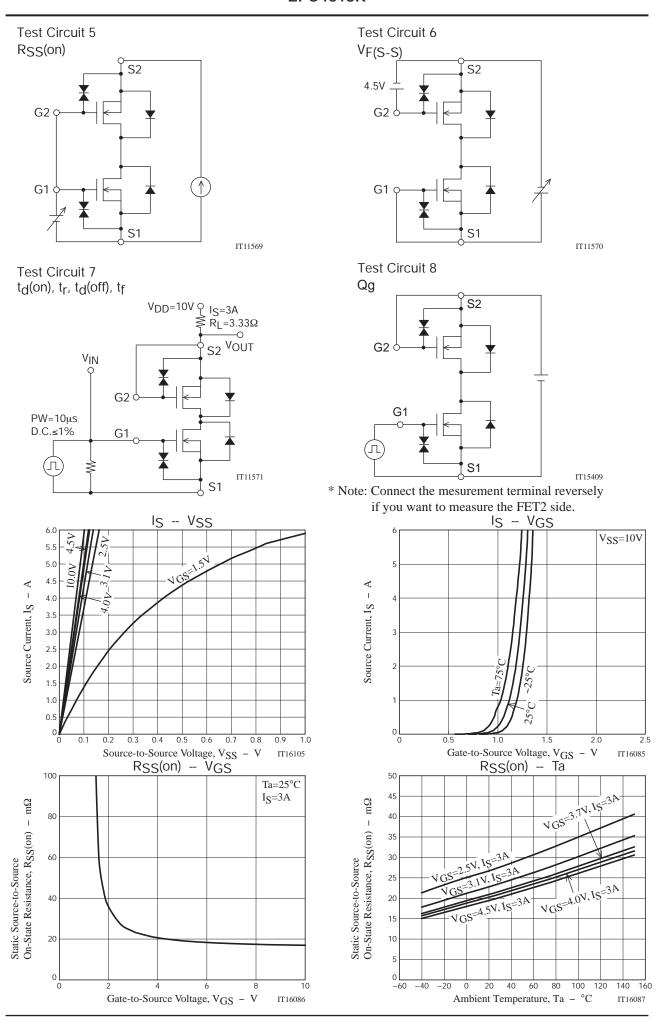


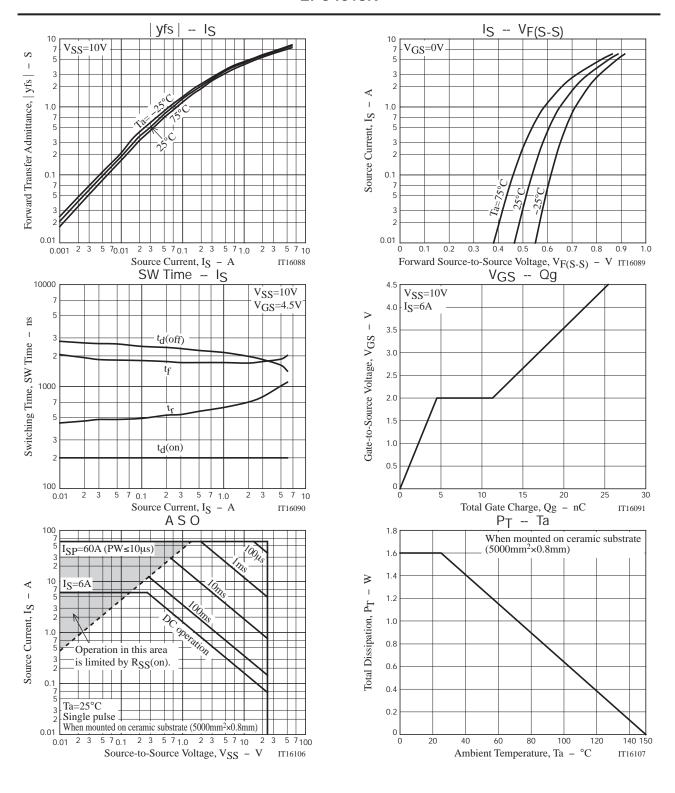
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Test Circuit 4



* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.





Note on usage: Since the EFC4618R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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